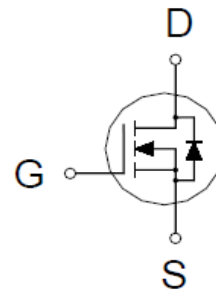
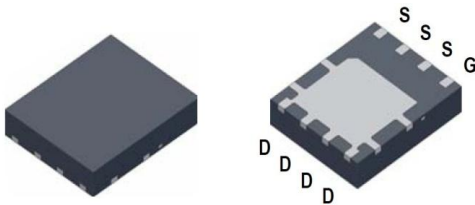


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N-Channel Enhancement Mode MOSFET

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
100V	12m Ω @ $V_{GS} = 10V$	40A



PDFN 5X6P

ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS	SYMBOL	LIMITS	UNITS	
Drain-Source Voltage	V_{DS}	20	V	
Gate-Source Voltage	V_{GS}	± 20	V	
Continuous Drain Current	I_D	$T_C = 25\text{ }^\circ\text{C}$	40	
		$T_C = 100\text{ }^\circ\text{C}$	26	
Pulsed Drain Current ¹	I_{DM}	110	A	
Continuous Drain Current	I_D	$T_A = 25\text{ }^\circ\text{C}$		12
		$T_A = 70\text{ }^\circ\text{C}$		9.4
Avalanche Current	I_{AS}	20		
Avalanche Energy	$L = 1\text{mH}$	E_{AS}	200	mJ
Power Dissipation	P_D	$T_C = 25\text{ }^\circ\text{C}$	40	W
		$T_C = 100\text{ }^\circ\text{C}$	20	
Power Dissipation ³	P_D	$T_A = 25\text{ }^\circ\text{C}$	4.1	W
		$T_A = 70\text{ }^\circ\text{C}$	2.6	
Operating Junction & Storage Temperature Range	T_J, T_{stg}	-55 to 150	$^\circ\text{C}$	

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$R_{\theta JA}$		30	$^\circ\text{C} / \text{W}$
Junction-to-Ambient ²	$R_{\theta JA}$		55	
Junction-to-Case	$R_{\theta JC}$		2.5	

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25\text{ }^\circ\text{C}$.

³The Power dissipation is based on $R_{\theta JA}$ $t \leq 10\text{ s}$ value.

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ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

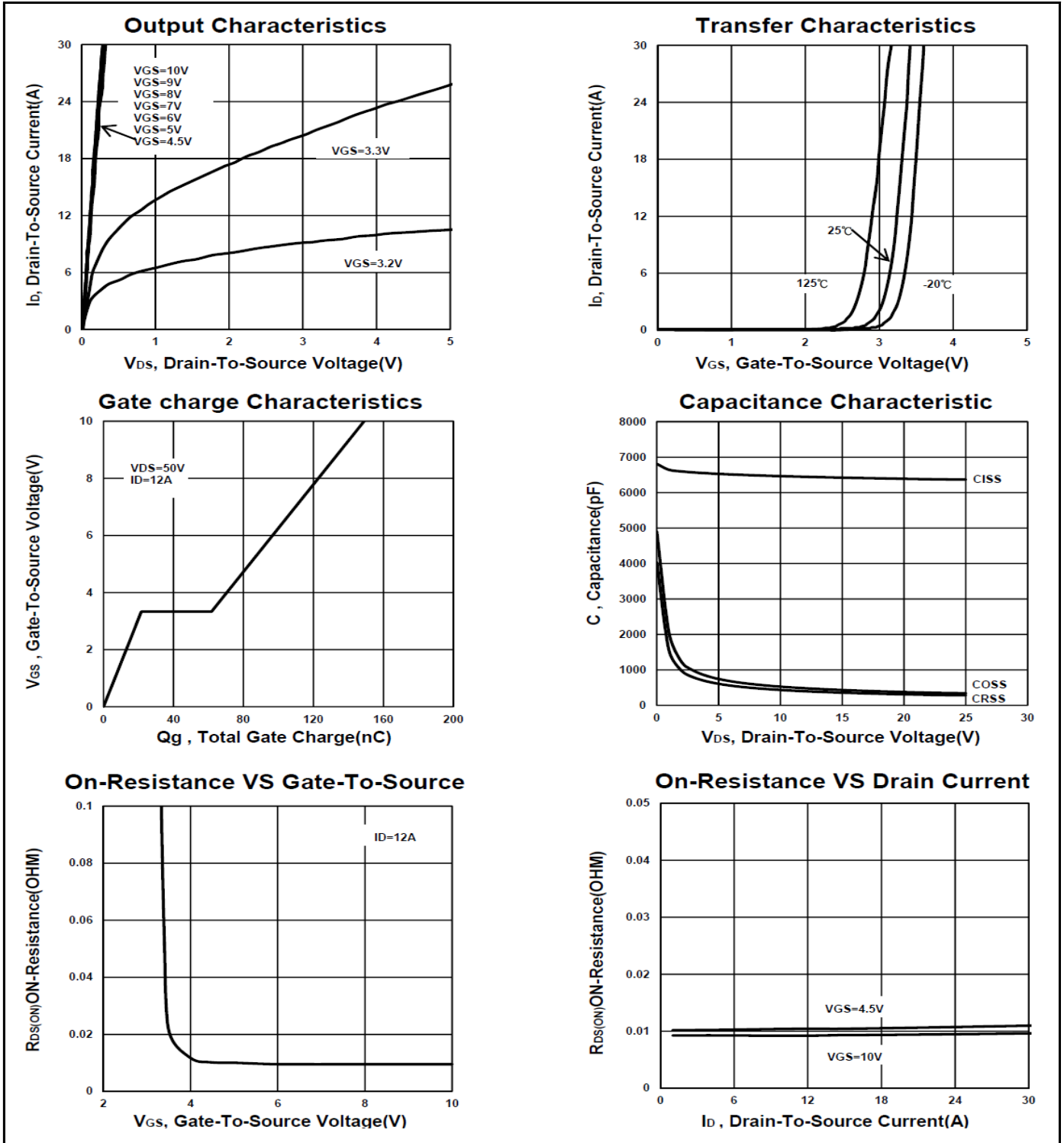
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNITS	
			MIN	TYP	MAX		
STATIC							
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100			V	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.3	1.8	2.3		
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80V, V _{GS} = 0V			1	μA	
		V _{DS} = 80V, V _{GS} = 0V, T _J = 55 °C			10		
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 10V, I _D = 12A		9	12	mΩ	
		V _{GS} = 4.5V, I _D = 12A		9.7	15		
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 12A		84		S	
DYNAMIC							
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		6410		pF	
Output Capacitance	C _{oss}			338			
Reverse Transfer Capacitance	C _{rss}			283			
Gate Resistance	R _g	V _{GS} = 0V, V _{DS} = 0V, f = 1MHz		0.73		Ω	
Total Gate Charge ²	Q _g	V _{GS} = 10V	V _{DS} = 50V, V _{GS} = 10V, I _D = 12A	153		nC	
		V _{GS} = 4.5V		76			
Gate-Source Charge ²	Q _{gs}	22					
Gate-Drain Charge ²	Q _{gd}	41					
Turn-On Delay Time ²	t _{d(on)}	V _{DS} = 50V, I _D ≅ 12A, V _{GS} = 10V, R _{GEN} = 6Ω		65			nS
Rise Time ²	t _r			220			
Turn-Off Delay Time ²	t _{d(off)}		30				
Fall Time ²	t _f		40				
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 °C)							
Continuous Current	I _S				33	A	
Forward Voltage ¹	V _{SD}	I _F = 12A, V _{GS} = 0V			1.3	V	
Reverse Recovery Time	t _{rr}	I _F = 12A, di _F /dt = 100A / μS		32		nS	
Reverse Recovery Charge	Q _{rr}			40		nC	

¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

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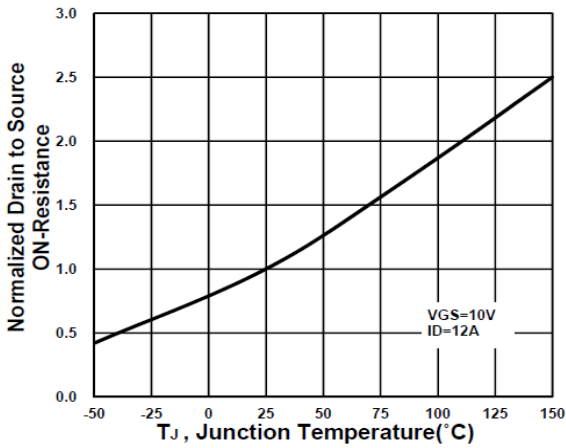
N-Channel Enhancement Mode MOSFET



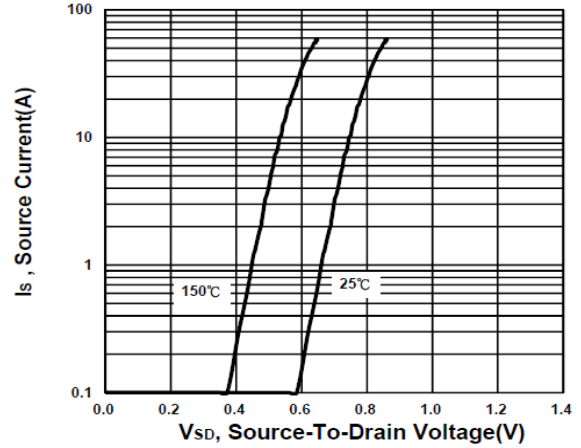
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N-Channel Enhancement Mode MOSFET

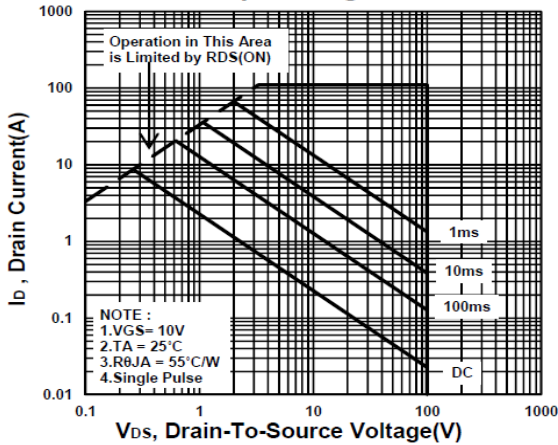
On-Resistance VS Temperature



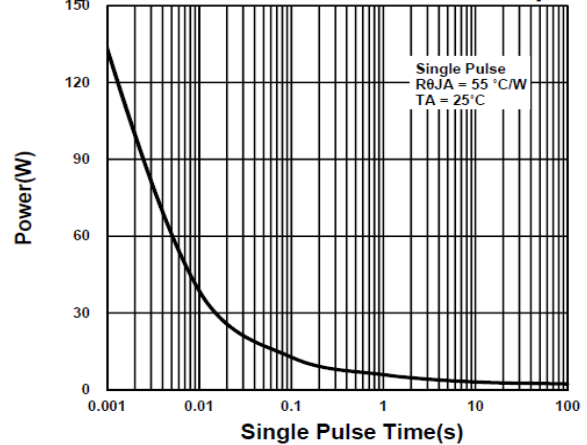
Source-Drain Diode Forward Voltage



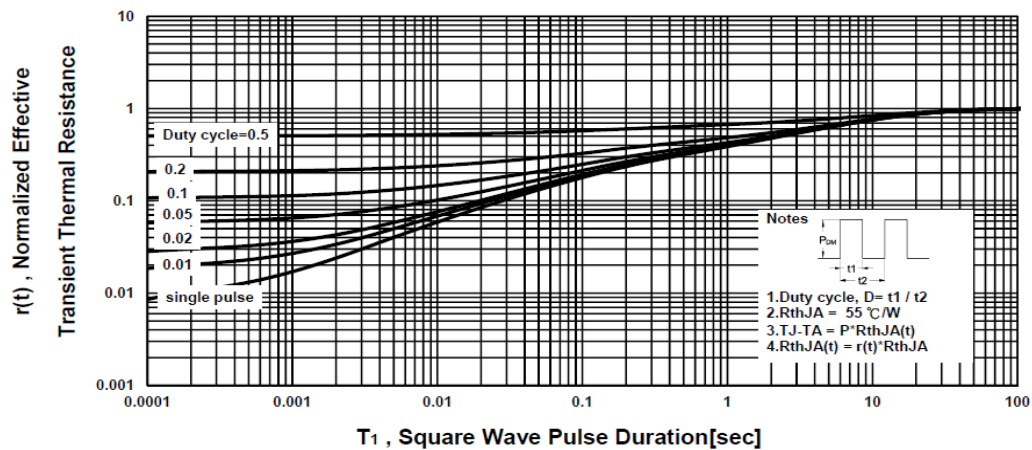
Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve



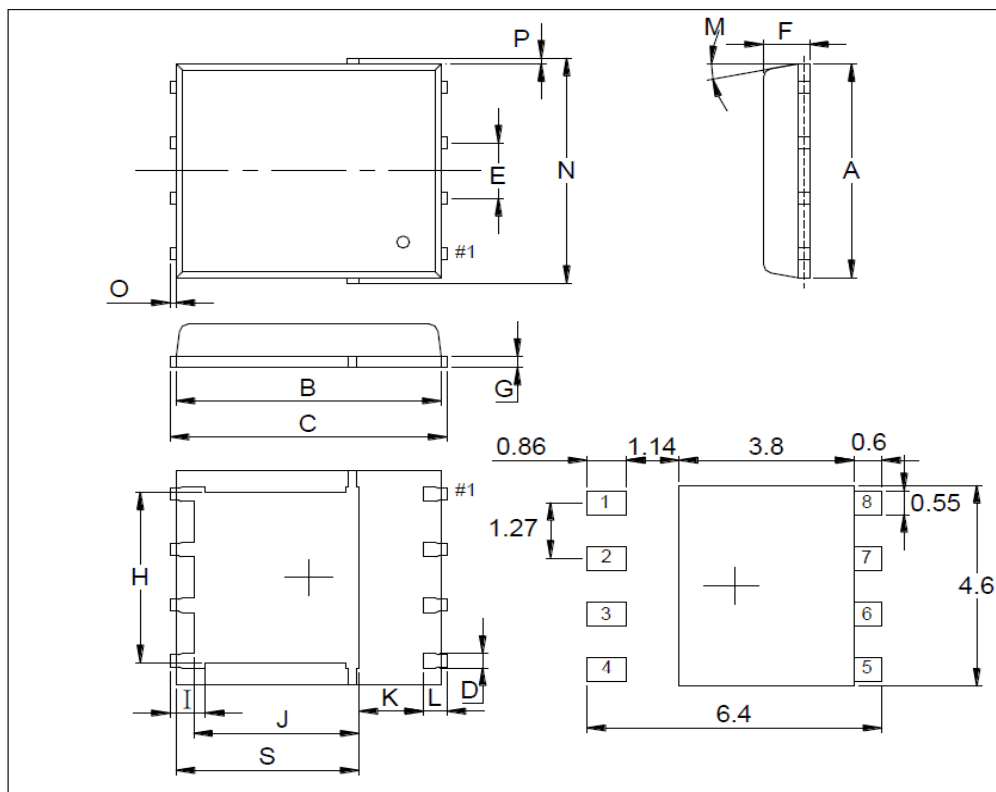
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Package Dimension

PDFN 5x6P MECHANICAL DATA

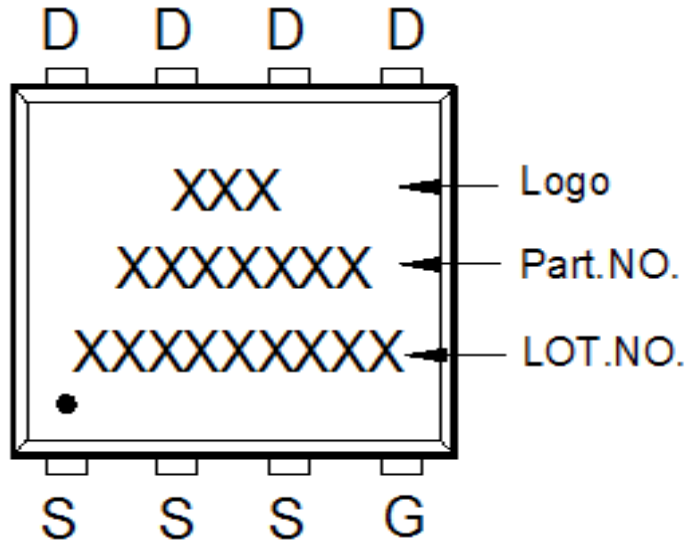
Dimension	mm			Dimension	mm		
	Min.	Typ.	Max.		Min.	Typ.	Max.
A	4.8		5.15	J	3.34		3.9
B	5.42		5.9	K	0.9		
C	5.9		6.35	L	0.38		0.711
D	0.3		0.51	M	0°		12°
E	1.17	1.27	1.37	N	4.8		5.4
F	0.8	1	1.2	O	0.05		0.36
G	0.15		0.35	P	0.05		0.25
H	3.67		4.31	S	3.73		4.19
I	0.38		0.71				



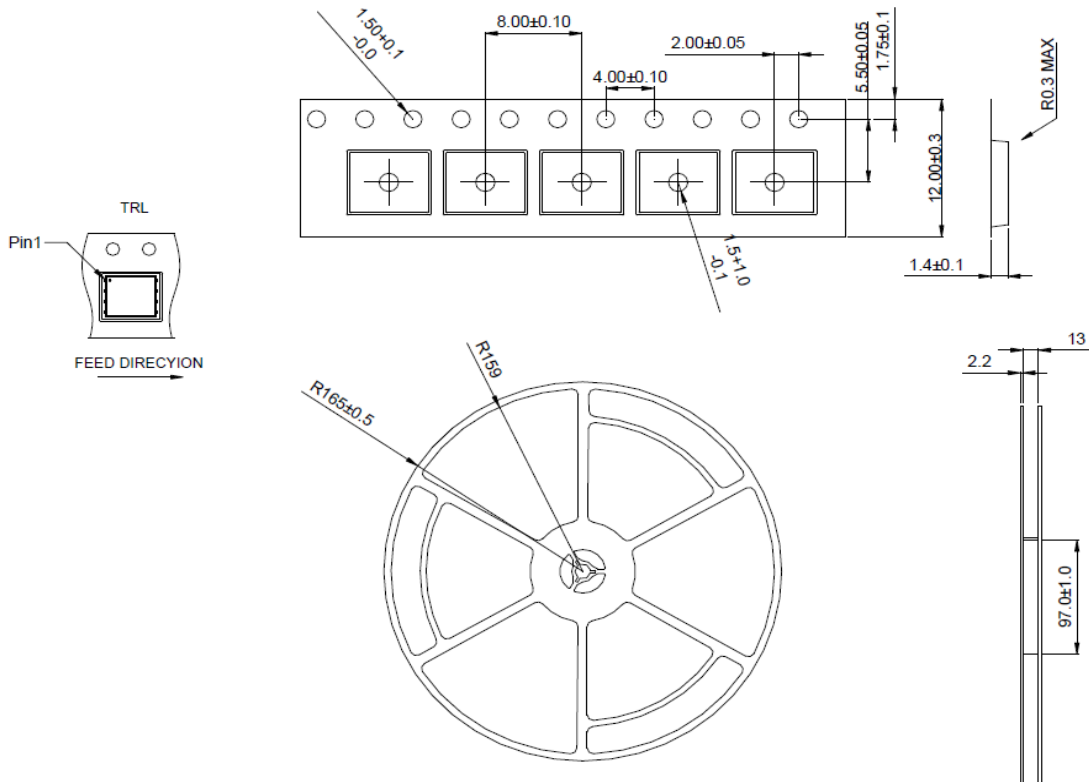
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A. Marking Information



B. Tape & Reel Information: 3000pcs/Reel

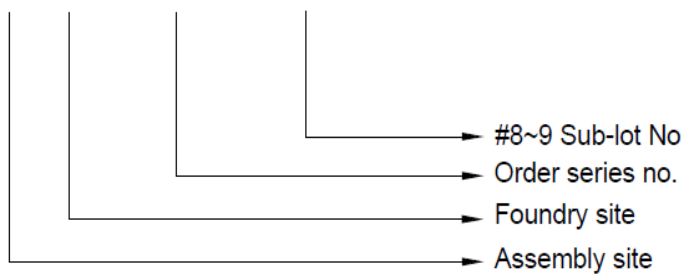


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C. Lot.No. & Date Code rule

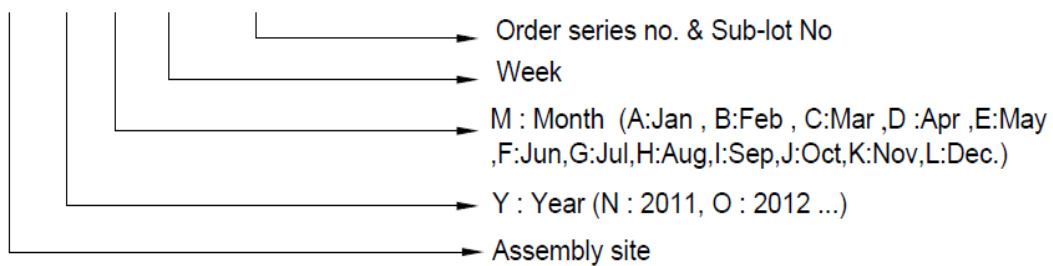
1.LOT.NO.

M N 15M21 03



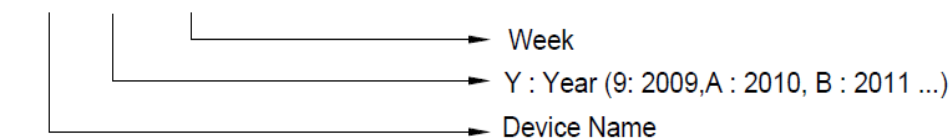
2.Date Code

D Y M X XXX



3.Date Code (for Small package)

XX Y WW





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D.Label rule

标签内容(Label content)



1	Label Size	30 * 90 mm
2	Font style	Times New Roman or Arial (或可区分英文"0"和数字"0", "G"和"Q"的字型即可)
3	Great Power	Height: 4 mm
4	Package	Height: 2 mm
5	Date	Height: 2 mm Shipping date: YYYY/MM/DD, ex. 2008/09/12
6	Device	Height: 3 mm (Max: 16 Digit)
7	Lot	Height: 3 mm (Max: 9 Digit) Sub lot
8	D/C	Height: 3 mm (Max: 7 Digit)
9	QTY	Height: 3 mm (Max: 6 Digit) Thousand mark is no needed
10	Pb Free label	 Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
11	Halogen Free label	 Diameter: 1 cm bottom color: Green Font color: Black Font style: Arial
12	Scan info	Device / Lot / D/C / QTY , Insert "/" between every parts. for example: P3055LDG/G12345601/GGG2301/2000 DPI (Dots per inch): Over 300 dpi Code : Code 128 Height: 6 mm at least